RENESAS HD74LVCZ245A

Octal Bidirectional Transceivers with 3-state Outputs

REJ03D0372–0300 (Previous ADE-205-228A (Z)) Rev.3.00 Aug. 18, 2004

Description

The HD74LVCZ245A has eight buffers with three state outputs in a 20 pin package. When (T / \overline{R}) is high, data flows from the A inputs to the B outputs, and when (T / \overline{R}) is low, data flows from the B inputs to the A outputs. A and B bus are separated by making enable input (\overline{OE}) high level.

When V_{CC} is between 0 and 1.5 V, the device is in the high impedance state during power up or power down.

Low voltage and high-speed operation is suitable at battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- $V_{CC} = 2.7$ to 5.5 V
- All inputs V_{IH} (Max) = 5.5 V (@V_{CC} = 0 to 5.5 V)
- All inputs / outputs $V_{I/O}$ (Max) = 5.5 V (@V_{CC} = 0 V or output off state)
- Typical V_{OL} ground bounce < 0.8 V (@V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@V_{CC} = 3.3 V, Ta = 25°C)
- High impedance state during power up and power down
- Power off disables outputs, permitting live insertion
- High output current ± 24 mA (@V_{CC} = 3.0 to 5.5 V)
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)		
HD74LVCZ245AFPEL	SOP–20 pin (JEITA)	FP–20DAV	FP	EL (2,000 pcs/reel)		
HD74LVCZ245ATELL	TSSOP-20 pin	TTP–20DAV	Т	ELL (2,000 pcs/reel)		

Function Table

Inputs

ŌĒ	T/R	Operation
L	L	B data to A bus
L	Н	A data to B bus
Н	Х	Z

H: High level

L: Low level

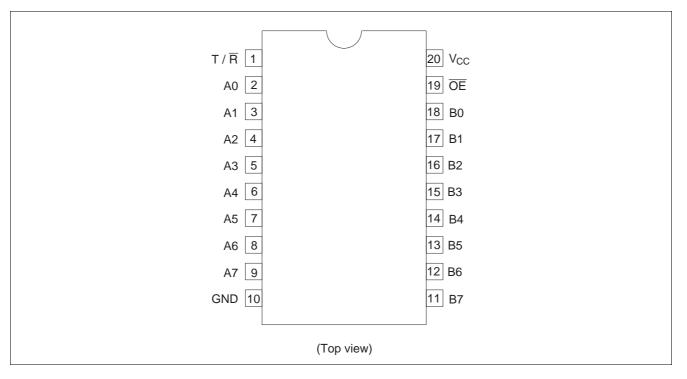
X: Immaterial

Z: High impedance



HD74LVCZ245A

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CC}	–0.5 to 7.0	V	
Input voltage	VI	–0.5 to 7.0	V	
Input / output voltage	V _{I/O}	–0.5 to 7.0	V	Output "Z" or V _{CC} : OFF
		–0.5 to V _{CC} +0.5		Output "H" or "L"
Input diode current	I _{IK}	-50	mA	V ₁ < 0
Output diode current	Ι _{ΟΚ}	-50	mA	V ₀ < 0
Output current	lo	±50	mA	
V _{CC} , GND current	I _{CC} or I _{GND}	±100	mA	
Storage temperature	Tstg	-65 to 150	°C	

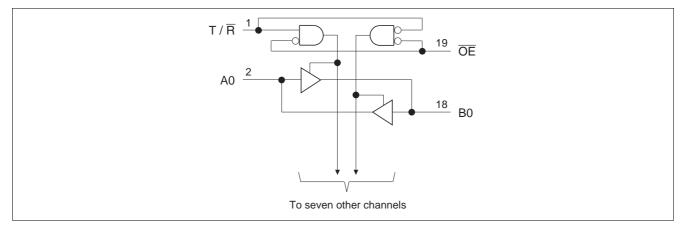
Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CC}	2.7 to 5.5	V	At operation
Input voltage	VI	0 to 5.5	V	
Input / output voltage	V _{I/O}	0 to 5.5	V	Output "Z" or V _{CC} : OFF
		0 to V _{CC}		Output "H" or "L"
Output current	I _{OH}	-12	mA	$V_{CC} = 2.7 V$
		-24 ^{*1}		V_{CC} = 3.0 to 5.5 V
	I _{OL}	12	mA	$V_{CC} = 2.7 V$
		24 ^{*1}		V_{CC} = 3.0 to 5.5 V
Input rise / fall time	t _r , t _f	0 to 6	ns / V	
Operating temperature	Та	-40 to +85	°C	

Note: 1. Duty cycle $\leq 50\%$

Logic Diagram





Electrical Characteristics

							$(Ta = -40 \text{ to } 85^{\circ}C)$
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIH	2.7 to 3.6	2.0	_	_	V	
		4.5 to 5.5	V _{CC} ×0.7	_	_	_	
	VIL	2.7 to 3.6	_	_	0.8	V	
		4.5 to 5.5	_	_	V _{CC} ×0.3	_	
Output voltage	V _{OH}	2.7 to 5.5	V _{CC} -0.2	_	_	V	I _{OH} = -100 μA
		2.7	2.2	_	_	_	I _{OH} = -12 mA
		3.0	2.4	_	_	_	
		3.0	2.2	_	_	_	I _{OH} = -24 mA
		4.5	3.8	_	_	_	
	V _{OL}	2.7 to 5.5	_	_	0.2		I _{OL} = 100 μA
		2.7	_	_	0.4	_	I _{OL} = 12 mA
		3.0	_	_	0.55	_	I _{OL} = 24 mA
		4.5	_	_	0.55	_	
Input current	I _{IN}	0 to 5.5	_	_	±5	μΑ	V _{IN} = 0 to 5.5 V
Off state output	l _{oz}	2.7 to 5.5	_	_	±5	μA	V _{OUT} = 0 to 5.5 V
current	IOZPU	0 to 1.5	_	_	±5	_	V _{OUT} = 0.5 to 5.5 V,
	IOZPD	1.5 to 0	_	_	±5	_	Output enable = don't care
Output leak current	IOFF	0	_	_	±5	μA	V_{IN} or $V_O = 5.5 V$
Quiescent supply	Icc	2.7 to 3.6	_	_	225	μA	$V_{IN} = 3.6$ to 5.5 V ^{*1} , $I_0 = 0$
current		2.7 to 5.5	_	_	350		$V_{IN} = V_{CC}$ or GND
	ΔI_{CC}	2.7 to 3.6	—	—	500	μA	V_{IN} = one input at (V _{CC} -0.6) V, other inputs at V _{CC} or GND
	<u> </u>	2.2		2.4		~F	· ·
Input capacitance	CIN	3.3	_	3.4	_	pF	$V_{IN} = V_{CC} \text{ or } GND$
Input / output capacitance	C _{I/O}	3.3	_	8.5	_	pF	$V_{OUT} = V_{CC} \text{ or } GND$

Note: 1. This applies in the disabled state only.



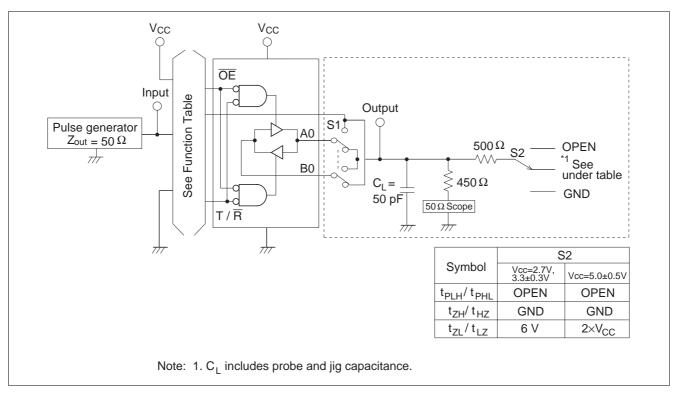
Switching Characteristics

							$(Ta = -40 \text{ to } 85^{\circ}C)$	
							FROM	то
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	(Input)	(Output)
Propagation delay time	t _{PLH}	2.7	_	—	7.3	ns	A or B	B or A
	t _{PHL}	3.3±0.3	1.5	—	6.3			
		5.0±0.5	—	—	4.8			
Output enable time	t _{ZH}	2.7			9.5	ns	ŌĒ	A or B
	t _{ZL}	3.3±0.3	1.5	—	8.5			
		5.0±0.5	—	—	7.0			
Output disable time	t _{HZ}	2.7	—	—	8.5	ns	OE	A or B
	t _{LZ}	3.3±0.3	1.7	_	7.5			
		5.0±0.5	_	_	6.5			
Between output pin skew *	t _{OSLH}	2.7			_	ns		
	t _{OSHL}	3.3±0.3		_	1.0			
		5.0±0.5			1.0			

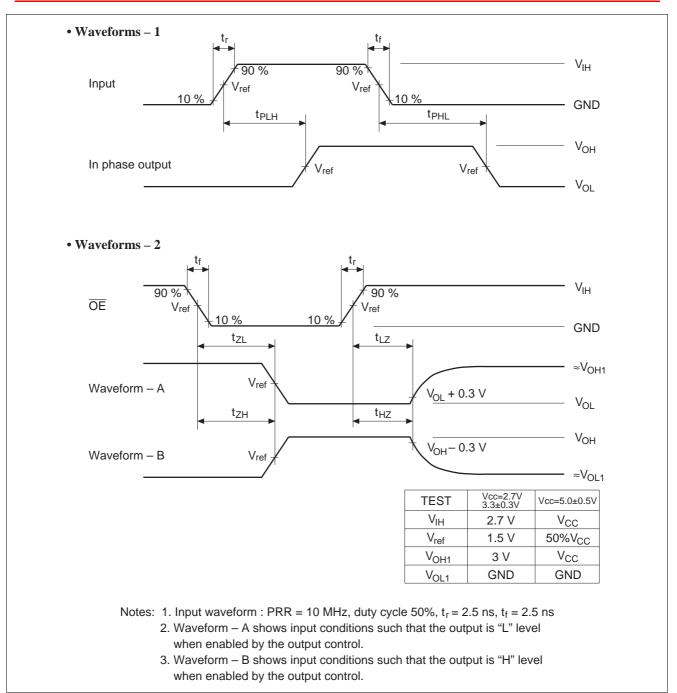
Note: 1. This parameter is characterized but not tested.

 $t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|$

Test Circuit



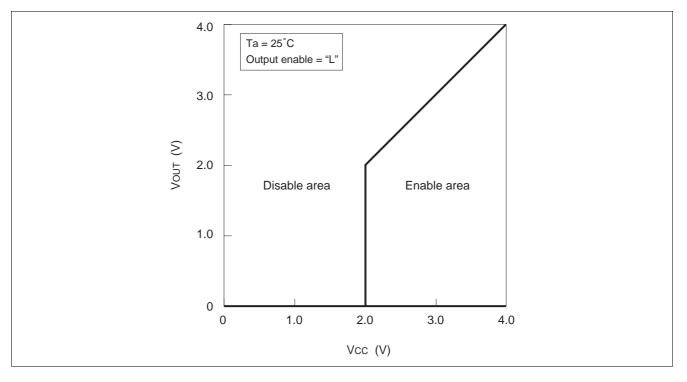
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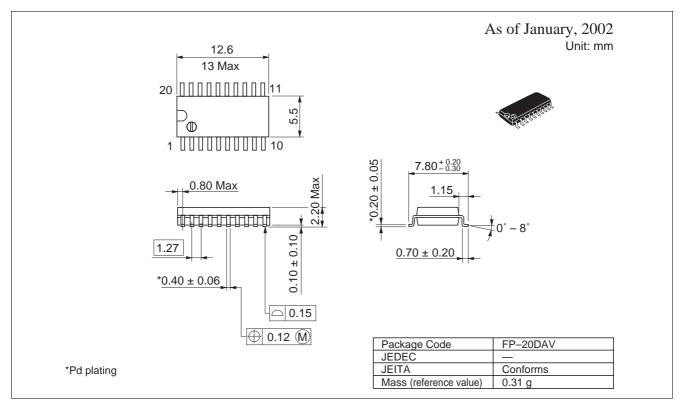
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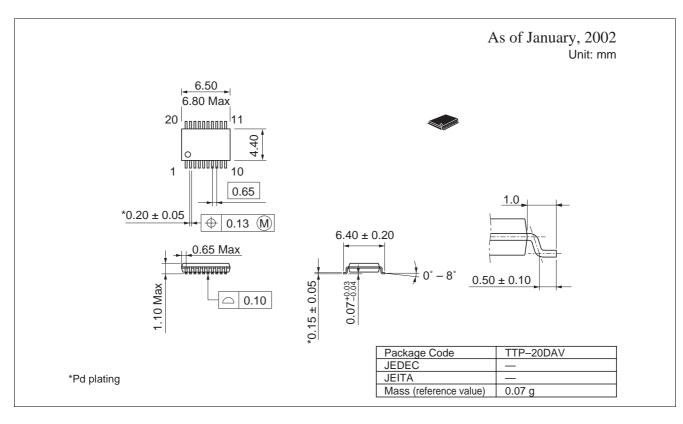
Power up / down Characteristics





Package Dimensions





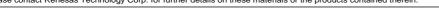
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